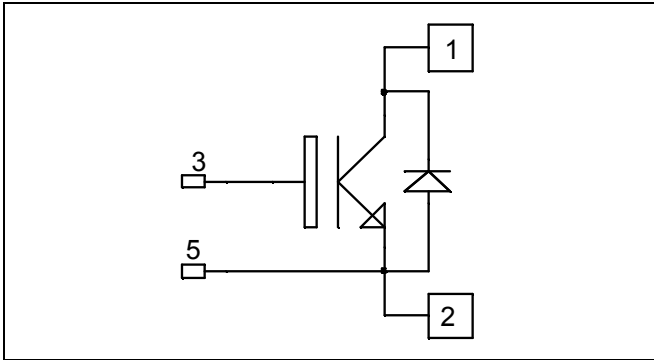


**Single switch
NPT IGBT Power Module**

**$V_{CES} = 600V$
 $I_C = 660A @ T_c = 80°C$**

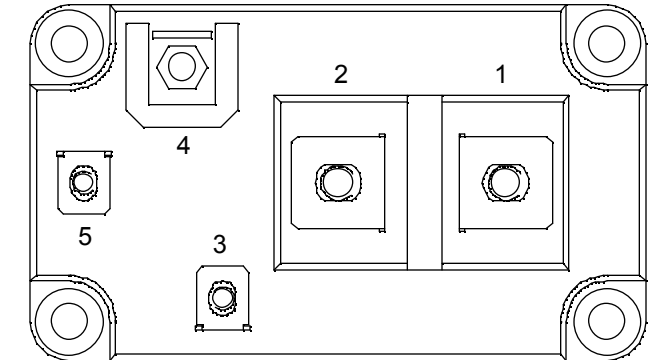


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
 - M6 connectors for power
 - M4 connectors for signal
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	$T_C = 25°C$	825	A
		$T_C = 80°C$	660	
I_{CM}	Pulsed Collector Current	$T_C = 25°C$	1100	
V_{GE}	Gate - Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	$T_C = 25°C$	2770	W
RBSOA	Reverse Bias Safe Operation Area	$T_j = 125°C$	1100A@520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 600\text{V}$	$T_j = 25^\circ\text{C}$		1	500	μA
			$T_j = 125^\circ\text{C}$		1		mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15\text{V}$ $I_C = 660\text{A}$	$T_j = 25^\circ\text{C}$		1.95	2.45	V
			$T_j = 125^\circ\text{C}$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 6\text{mA}$	4.5	5.5	6.5	V	
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}, V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		36		nF
C_{res}	Reverse Transfer Capacitance			3.2		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 800\text{A}$ $R_G = 4.7\Omega$		210		ns
T_r	Rise Time			86		
$T_{d(off)}$	Turn-off Delay Time			420		
T_f	Fall Time			83		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 800\text{A}$ $R_G = 4.7\Omega$		250		ns
T_r	Rise Time			93		
$T_{d(off)}$	Turn-off Delay Time			450		
T_f	Fall Time			95		
E_{on}	Turn on Energy			18		mJ
E_{off}	Turn off Energy			25		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_F	Diode Forward Voltage	$I_F = 800\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$		1.25	1.6	V
			$T_j = 125^\circ\text{C}$		1.2		
Q_{rr}	Reverse Recovery Charge	$I_F = 800\text{A}$ $V_R = 300\text{V}$ $di/dt = 4000\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		52		μC
			$T_j = 125^\circ\text{C}$		87		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case	IGBT			0.045	$^\circ\text{C}/\text{W}$
		Diode			0.085	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}, I_{isol} < 1\text{mA}, 50/60\text{Hz}$	2500			V	
T_j	Operating junction temperature range	-40		150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		125		
Torque	Mounting torque	M6	3		5	N.m
		M4	1		2	
Wt	Package Weight			420	g	

